

Customer No.: 31561
Application No.: 10/605,122
Docket No.:9165-US-PA-OP

Specification Amendment

Please replace paragraph [0031] of the disclosure with the following paragraph:

[0031] Referring to Fig. 2D, a lightly doped drain (LDD) region 210 is formed in the strained silicon layer 204 at both sides of the gate structure 208. For example, once the gate structure 208 is established, the gate structure 208 serves to mask an lightly doped drain (LDD) implant into a certain thickness of the strained silicon layer 204 at both sides of the gate structure 208 to form the LDD region 210. Alternatively, the lightly doped region 210 is formed occupying the entire thickness of the strained silicon layer 204 at both sides of the gate structure 208 as shown in Figure 3A. The ~~LDD~~ LDD implant comprises, for example, n-type species, such as, arsenic ions, for forming an NMOS transistor. Further, the dosage and the implant energy are chosen such that the LDD region 210 is shallower than and of lighter concentration than the subsequent source/drain region.